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Applicant Mascarenhas, Angelo

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U. S. PATENT DOCUMENTS

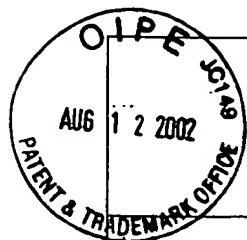
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6 0 0 2 2 0 2	12/99	Mayer <i>et al.</i>	313	420	
	5 9 8 6 2 8 8	11/99	Hasegawa	257	94	
	5 9 6 3 5 7 1	10/99	Wingreen	372	45	
	5 8 9 5 2 2 5	4/99	Kidoguchi <i>et al.</i>	438	47	
	5 7 7 6 7 9 3	7/98	Lee <i>et al.</i>	438	35	
	5 7 2 8 2 3 1	3/98	Negami <i>et al.</i>	148	33	
	5 4 5 3 4 0 4	9/95	Leedy	437	203	
	5 3 8 7 5 4 4	2/95	Hayafuji	437	151	
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	5 2 3 1 2 9 8	7/93	Daly	257	191	
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	5 0 2 8 5 6 1	7/91	Ramath <i>et al.</i>	437	105	
	4 9 3 9 1 0 3	7/90	Szolgyemy	437	151	
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	4 4 0 0 2 2 1	8/83	Rahilly	148	1.5	
	4 2 8 4 9 6 2	8/81	Esterowitz <i>et al.</i>	331	94.5F	

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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER	DATE CONSIDERED

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